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irradiating the amorphous semiconductor film with a CW laser having a wavelength of 532 nm to crystallize the amorphous semiconductor film; and

patterning the crystallized semiconductor film to form an active layer including at least a channel formation region.

22. (New) The method according to claim 21 wherein said amorphous semiconductor film comprises amorphous silicon.

23. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a CW laser having a wavelength of 355 nm to crystallize the amorphous semiconductor film; and

patterning the crystallized semiconductor film to form an active layer including at least a channel formation region.

24. (New) The method according to claim 23 wherein said amorphous semiconductor film comprises amorphous silicon.

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25. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a second harmonic of a CW laser comprising Nd to crystallize the amorphous semiconductor film; and

patterning the crystallized semiconductor film to form an active layer including at least a channel formation region.

26. (New) The method according to claim 25 wherein said amorphous semiconductor film comprises amorphous silicon.

27. (New) The method according to claim 25 wherein said CW laser comprising Nd is an Nd:YAG laser.

28. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming an amorphous semiconductor film over a substrate;

irradiating the amorphous semiconductor film with a third harmonic of a CW laser comprising Nd to crystallize the amorphous semiconductor film; and

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patterning the crystallized semiconductor film to form
an active layer including at least a channel formation region.

29. (New) The method according to claim 28 wherein said
amorphous semiconductor film comprises amorphous silicon.

30. (New) The method according to claim 28 wherein said CW
laser comprising Nd is an Nd:YAG laser. ~
